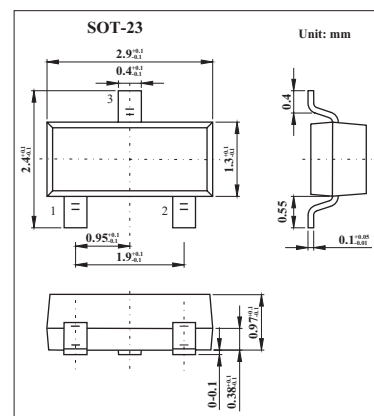


Silicon PIN Diodes

BA779;BA779S

■ Features

- Wide frequency range 10 MHz to 1 GHz

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Value	Unit
Reverse Voltage	V_R		30	V
Forward Current	I_F		50	mA
Junction Temperature	T_j		125	$^\circ\text{C}$
Storage temperature range	T_{stg}		-55 to +125	$^\circ\text{C}$
Junction ambient	R_{thJA}	on PC board 50mm×50mm×1.6mm	500	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F = 20\text{ mA}$			1	V
Reverse Current	I_R	$V_R = 30\text{ V}$			50	nA
Diode capacitance	C_D	$f = 100\text{ MHz}, V_R = 0$			0.5	pF
Differential forward resistance	r_f	$f = 100\text{ MHz}, I_F = 1.5\text{ mA}$			50	Ω
Reverse impedance	z_r	$f = 100\text{ MHz}, V_R = 0$	5 9			K Ω
Minority carrier lifetime	τ	$I_F = 10\text{ mA}, I_R = 10\text{ mA}$		4		$\mu\text{ s}$